

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	309	(memory and logic adj1 device\$1).ti.	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 16:56
2	BRS	L2	29246	first near1 transistor and second adj1 transistor	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 16:47
3	BRS	L3	5	1 and 2	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 16:47
4	BRS	L4	48	(memory near1 device\$1 and logic adj1 device\$1).ti.	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 16:46
5	BRS	L5	48	(memory near1 device\$1 and logic adj1 device\$1).ti.	USPAT; US-PGP; UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 16:56

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	16	9	5 and transistor	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 16:45
7	BRS	L7	3338	memory nearl device\$1 and logic adjl device\$1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 16:57
8	BRS	18	128	dual adjl gate adjl oxide\$1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:08
9	BRS	19	16	7 and 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 16:58
10	BRS	21	11	transistor	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:08

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L11	39264	gate ad*1 oxide\$1	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM_TD B	2002/03/31 17:06
12	BRS	L12	422	7 and 11	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM_TD B	2002/03/31 17:06
13	BRS	L13	59	transistor	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM_TD B	2002/03/31 17:06
14	BRS	L14	53	13 and thickness	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM_TD B	2002/03/31 17:06
15	BRS	L15	53	14 and (oxidation or oxide\$3)	USPAT; US-PGP UB; EPO; JPO; DERWEN; T; IBM_TD B	2002/03/31 17:06

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	11	15 and (high adj1 temperature)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:13
17	BRS	L17	694	(dielectric adj1 layer) near5 (gate adj1 oxide\$1)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:23
18	BRS	L19	7	15 and 18	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:14
19	BRS	L18	7	15 and 17	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:14
20	BRS	L20	893	((dielectric or silicon adj1 dioxide) adj1 layer) near5 (gate adj1 oxide\$1)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:24

	Type	L #	Hits	Search Text	DBs	Time Stamp
21	BRS	L21	31	7 and 20	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:24
22	BRS	L22	28	21 and transistor	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:27
23	BRS	L23	14305	advanced adjl min. 1371 devices	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:29
24	BRS	L24	193	7 and 23	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:28
25	BRS	L25	14305	advanced adjl min. 1371 devices	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:29

	Type	L #	Hits	Search Text	DBs	Time Stamp
26	BRS	126	3	4551910.pn.	USPAT; US-PGP JB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:43
27	BRS	127	3	4551910.pn.	USPAT; US-PGP JB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:43
28	BRS	128	2380	gate adj1 oxide\$1.ti.	USPAT; US-PGP JB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:43
29	BRS	129	14	7 and 28	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 17:43
30	BRS	130	3	5057449.pn.	USPAT; US-PGP JB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 18:10

	Type	L #	Hits	Search Text	DBs	Time Stamp
31	BRS	L31	53	31 and 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 18:47
32	BRS	L32	53	31 and 7	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 18:47
33	BRS	L33	2	1 and (silicon adj1 nitride) near5 (oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 18:50
34	BRS	L34	6	1 and (silicon adj1 nitride) near5 (boron and oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 18:50
35	BRS	L35	6	7 and (silicon adj1 nitride) near5 (boron and oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 18:50

	Type	L #	Hits	Search Text	DBs	Time Stamp
36	ERS	137	17	7 and (silicon adj1 nitride) near5 (boron or oxidized)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 18:51
37	ERS	138	41	7 and (silicon adj1 nitride) near3 (boron or oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 18:51
38	ERS	138	41	7 and (silicon adj1 nitride) near3 (oxidized or oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 19:26
39	ERS	139	15	7 and (silicon adj1 oxide) near3 (oxidized or oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 19:29
40	ERS	140	17	7 and (silicon adj1 dioxide) near3 (oxidized or oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 19:30



	Type	L #	Hits	Search Text	DBs	Time Stamp
41	BRS	L41	33	7 and (gate adj1 oxide) near3 (oxidized or oxidation)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 19:51
42	BRS	L42	14	41 and (high near1 temperature)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 20:05
43	BRS	L43	12	7 and (oxide\$1 or dioxide) near1 (oxidation or oxidized)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 20:06
44	BRS	L44	75	43 and (high adj1 temperature)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 20:06
45	BRS	L45	229	44 and transistor	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/31 20:07